

Contents

List of Contributors

ix

Preface

xi

Chapter 1 Trends in MOS Integrated Circuit Technology

Thomas F. McNelly

I.	Historical Perspective	1
II.	Device Scaling	2
III.	Trends in FET Design	3
IV.	Isolation	5
V.	Lithography	7
VI.	Ion Implantation	8
VII.	Dielectrics	8
VIII.	Interconnect	9
IX.	Contacts	10
X.	Reliability	11
XI.	BiCMOS	12
XII.	Memory Technology	13
XIII.	The Future	14
	References	14

Chapter 2 Laser Beam Processing and Wafer-Scale Integration

Simon S. Cohen and Glenn H. Chapman

I.	Introduction	19
II.	Theoretical Considerations	23
III.	Results for the LIDL Process	56
IV.	Laser Beam Processing in IC Repair and Customization	84
	References	108

Chapter 3 Electron Beam Processing**J. J. Muray**

I.	Introduction	113
II.	Interaction of Electrons with Matter	114
III.	Components for Electron Beam Machines	127
IV.	Multibeam E-Beam Machines	141
V.	Applications Involving Low Electron Energies	147
VI.	Chemical Processing	150
	References	155

Chapter 4 Ion Beam Techniques and Applications**L. R. Harriott**

I.	Introduction	157
II.	Sources for Broad-Area Ion Beams	159
III.	Sources for Submicrometer Beams	162
IV.	Parallel Processing with Broad-Area Beams	169
V.	Serial Processing with Finely Focused Beams	178
VI.	Summary	202
	References	203

**Chapter 5 Silicon Molecular Beam Epitaxy:
Capabilities and Trends****S. L. Delage**

I.	Introduction	208
II.	Si MBE Technology	208
III.	Growth Mechanisms and Surface Preparation	214
IV.	Silicon Doping	221
V.	Polycrystalline Silicon	235
VI.	Application of Si MBE	237
VII.	Conclusion	249
	References	250

Chapter 6 Chemical Beam Epitaxy**W. T. Tsang**

I.	Introduction	256
II.	CBE System Design	260
III.	Substrate Preparation for Growth	273
IV.	Growth Kinetics of CBE	274
V.	Quality of Epilayers	306
VI.	Growth of Epilayers Using Group Alkyls	323
VII.	GaInAs/InP and GaAs/AlGaAs Quantum Wells and Superlattices	324
VIII.	Doping Control	333
IX.	Device Applications	341
X.	Concluding Remarks	353
	References	353

**Chapter 7 Ion Implantation for VLSI
Nicholas R. White**

I.	Introduction	360
II.	Commercial Ion Implanters	361
III.	Ion Beam Production and Acceleration	369
IV.	Implantation Physics	385
V.	Problems Associated with Ion Implantation	394
VI.	Endstation Design	411
VII.	Ion Implanter System Design	425
	References	435

**Chapter 8 Incoherent Radiation and Its Applications
(Visible, UV, X rays)
Dietrich Meyerhofer**

I.	Introduction	440
II.	Pattern Replication	442
III.	Optical Imaging	449
IV.	Photolithographic Tools	455
V.	Deep-UV Lithography	463
VI.	X-ray Lithography	467
VII.	Thermal Processing with Incoherent Radiation	472
VIII.	Conclusion	475
	References	475

**Chapter 9 Electron Beam Testing: An Outline of Techniques
A. Gopinath**

I.	Introduction	477
II.	Introduction to the Scanning Electron Microscope	479
III.	Qualitative Voltage Contrast	483
IV.	Voltage Contrast Linearization for Potential Measurements	485
V.	Estimate of Minimum Measurable Voltage	501
VI.	Observation of Fast Voltage Waveforms and Dynamic Voltage Distributions Using a Pulsed Beam Probe	507
VII.	Electron Beam Pulsing in the Electron-Optical Column	509
VIII.	Stroboscopic and Sampling Mode Operation	521
IX.	Other Modes with Synchronous and Asynchronous Pulsed Beams	525
X.	Summary	528
	References	529